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(54) SEMICONDUCTOR PACKAGE DEVICE

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(57)ABSTRACT

A semiconductor package device includes a first semiconductor package, a second semiconductor package, and first connection terminals between the first and second semiconductor packages. The first semiconductor package includes a lower redistribution substrate, a semiconductor chip, and an upper redistribution substrate vertically spaced apart from the lower redistribution substrate across the semiconductor chip. The upper redistribution substrate includes a dielectric layer, redistribution patterns vertically stacked in the dielectric layer and each including line and via parts, and bonding pads on uppermost redistribution patterns. The bonding pads are exposed from the dielectric layer and in contact with the first connection terminals. A diameter of each bonding pad decreases in a first direction from a central portion at a top surface of the upper redistribution substrate to an outer portion at the top surface thereof. A thickness of each bonding pad increases in the first direction.

